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**Sakai et al.**

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(54) **ELECTRONIC COMPONENT AND METHOD OF MANUFACTURING THE SAME**

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**H01F 5/00** (2006.01)  
**H01F 27/28** (2006.01)  
**H01F 17/00** (2006.01)

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CPC ..... **H01F 5/003** (2013.01); **H01F 17/0013**  
(2013.01); **H01F 2017/002** (2013.01)  
USPC ..... **336/200**; 336/232

(58) **Field of Classification Search**  
USPC ..... 336/200, 232  
See application file for complete search history.

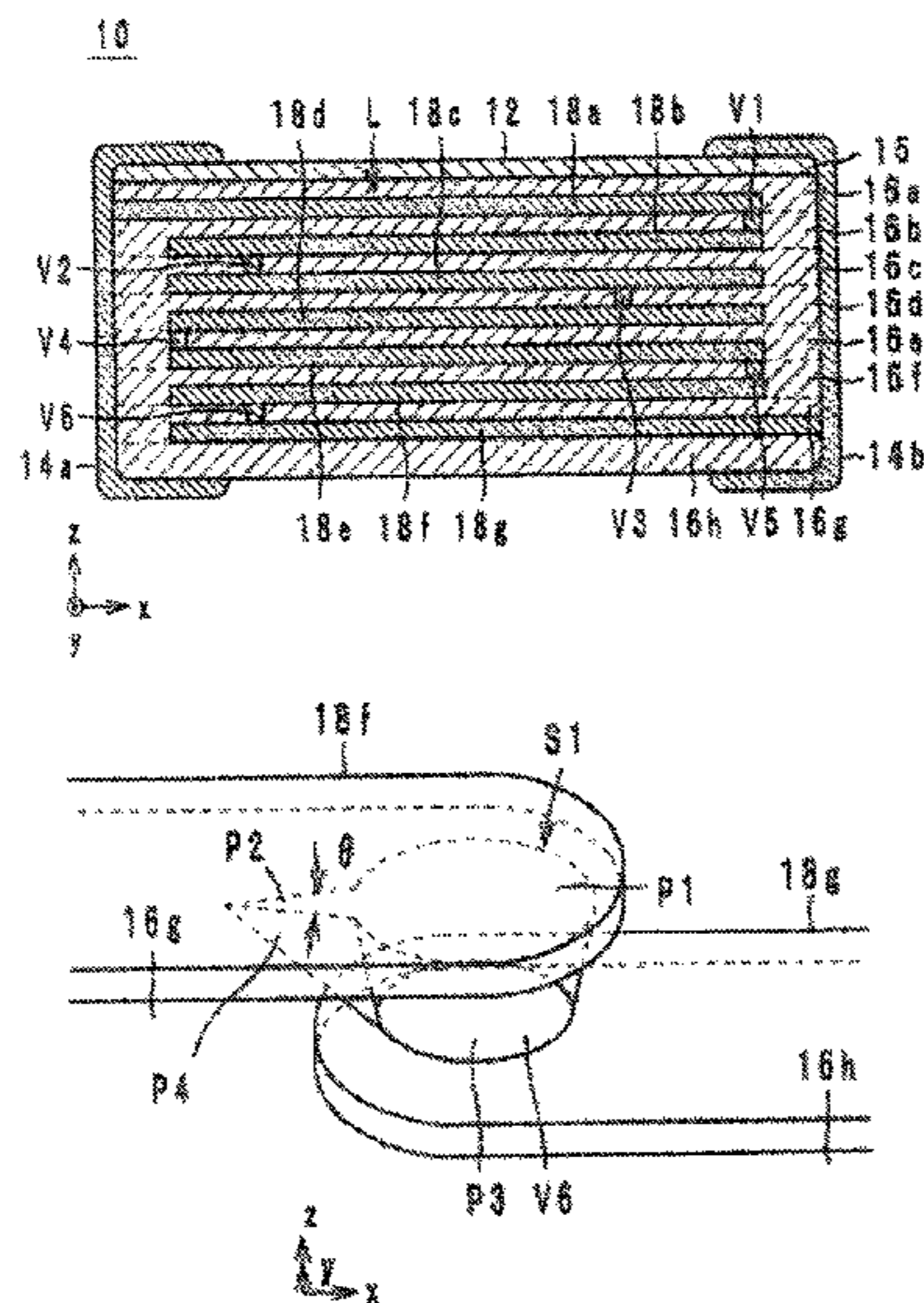
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(57) **ABSTRACT**

Provided is an electronic component that can suppress the occurrence of disconnections between line conductor layers and via hole conductors and a method of manufacturing the electronic component. A multilayer body is formed by stacking insulating layers. A conductor layer is provided on a first insulating layer. A line conductor layer is provided on a second insulating layer that is provided on an upper side of the first insulating layer in a stacking (z-axis) direction. A via hole conductor connects an end portion of the line conductor layer to the conductor layer and extends through the second insulating layer in the z-axis direction. In the via hole conductor, a connection surface connected to the line conductor layer is formed of a circular portion and a protrusion. The protrusion protrudes from the circular portion in the x-axis direction in which the line conductor layer extends from the end portion.

**4 Claims, 8 Drawing Sheets**



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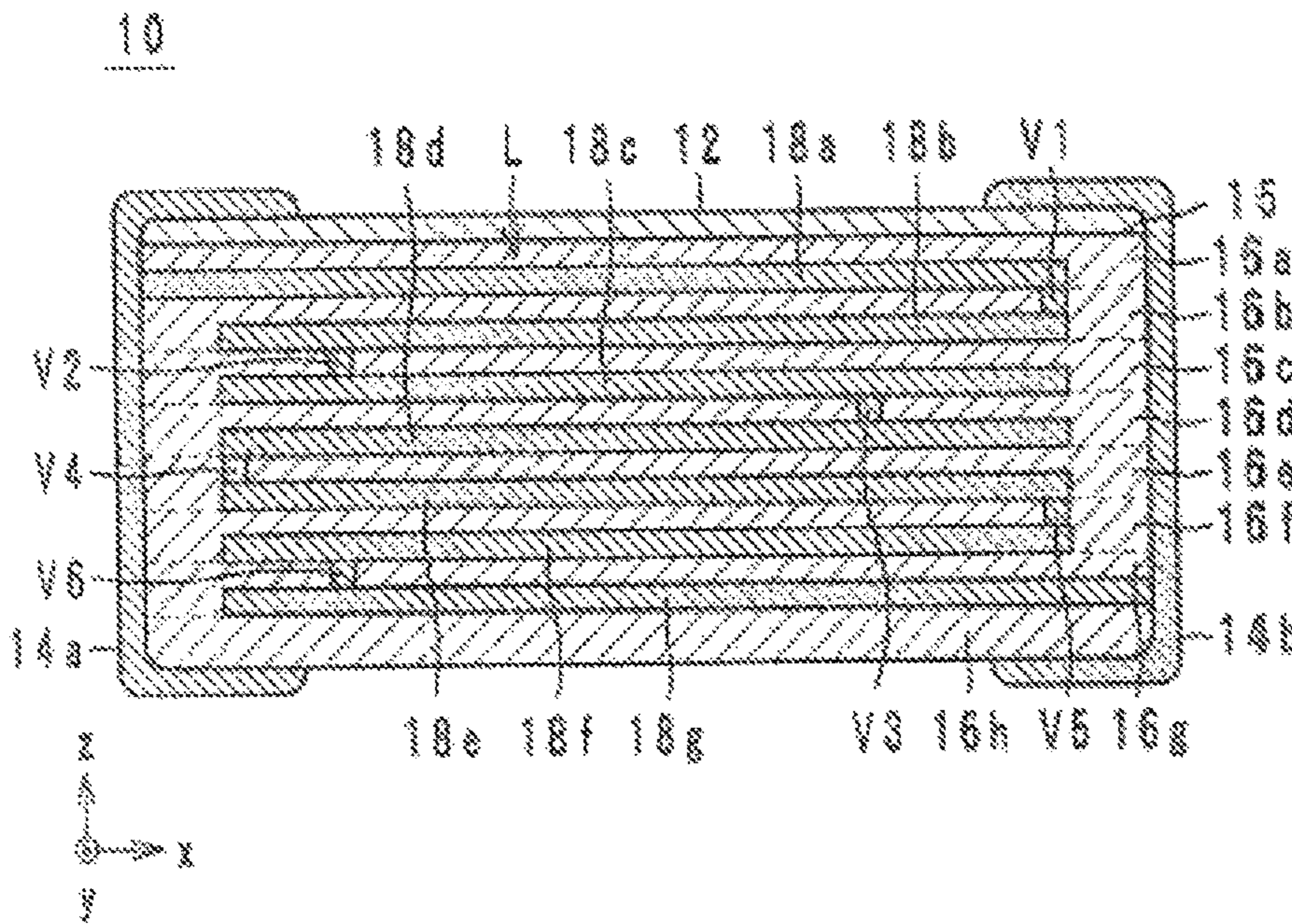


FIG.1

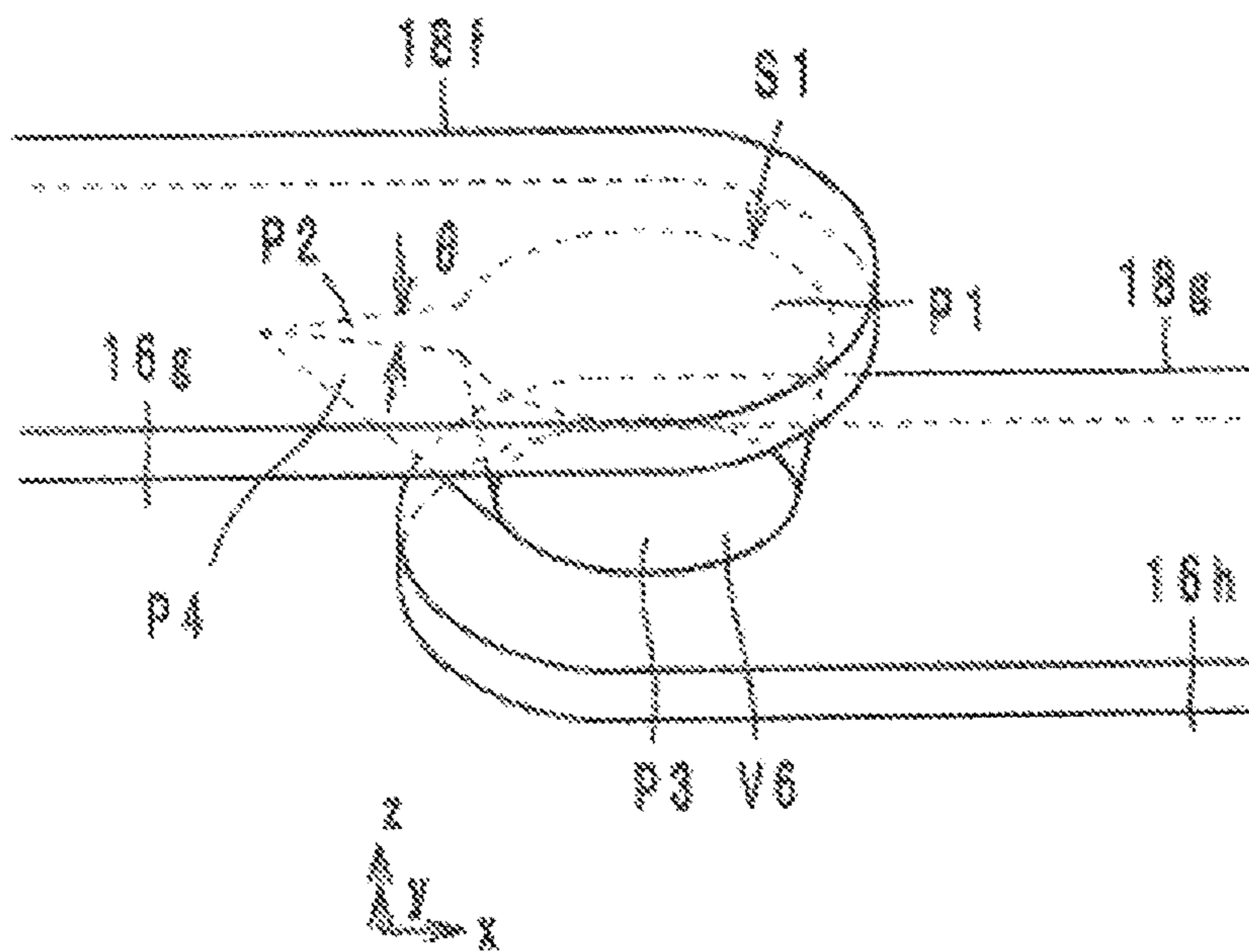


FIG.2

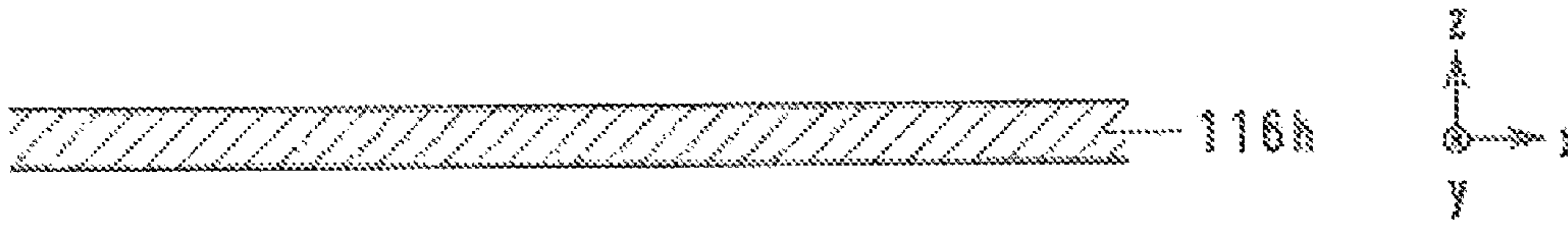


FIG. 3A

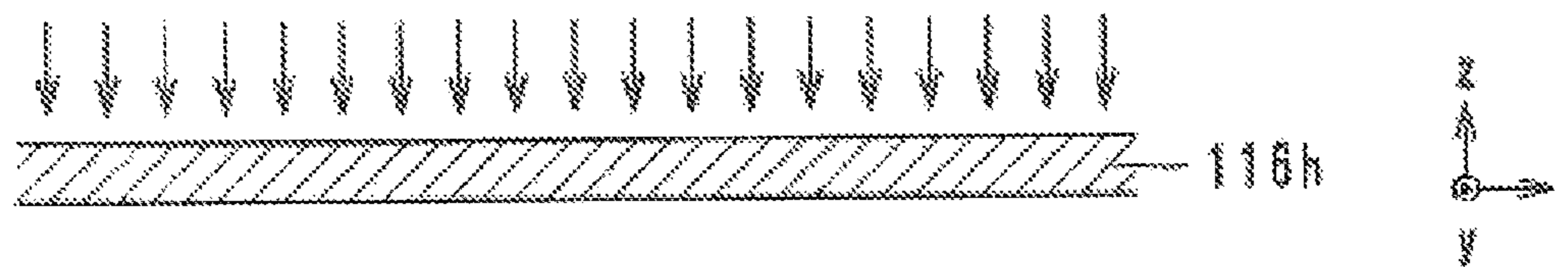


FIG. 3B

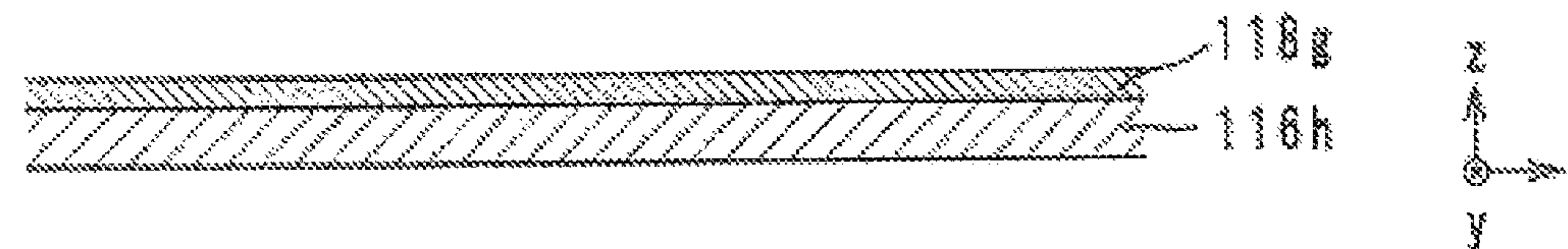


FIG. 3C

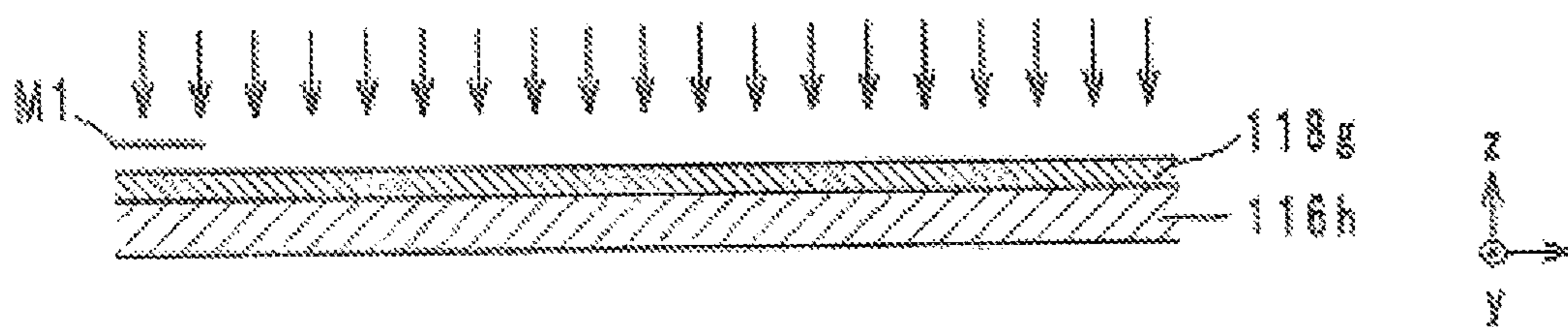


FIG. 3D

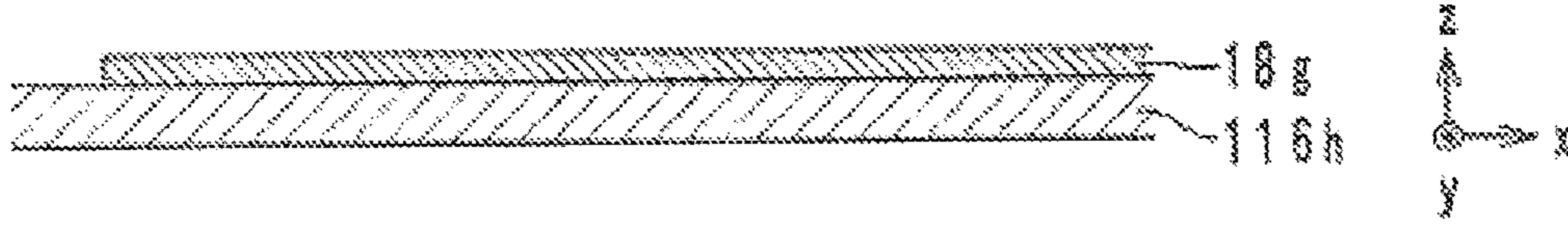


FIG.4A

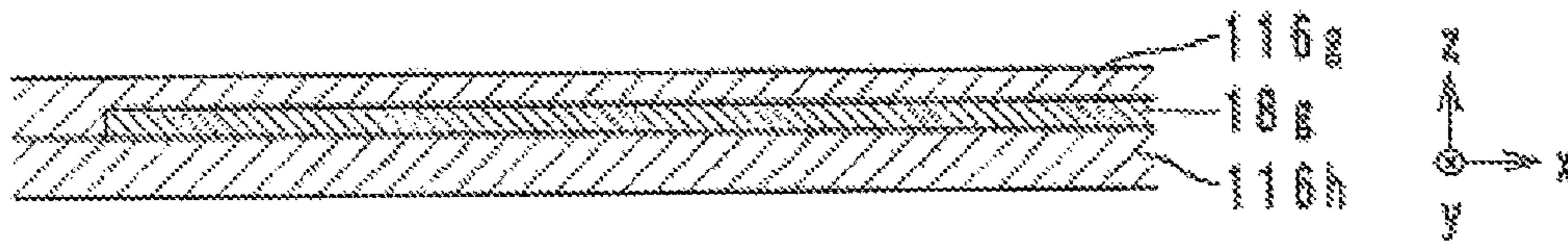


FIG.4B

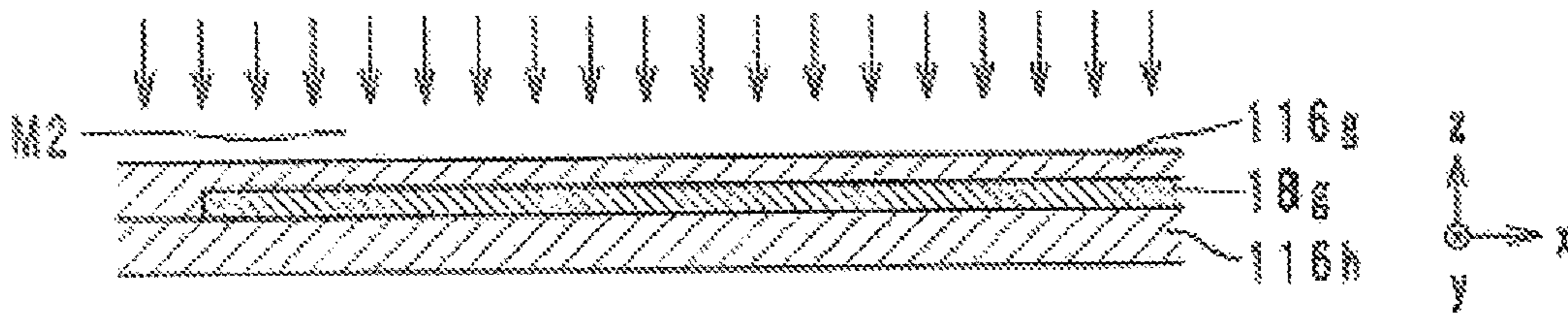


FIG.4C

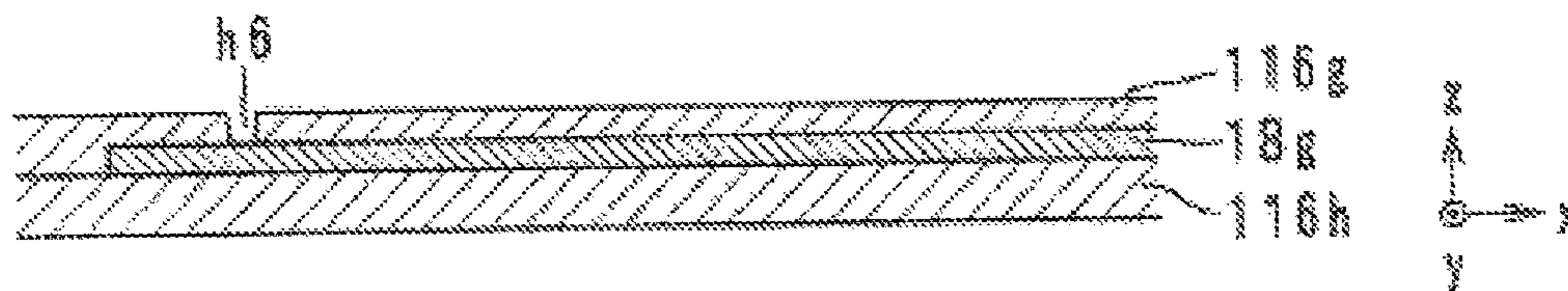


FIG.4D

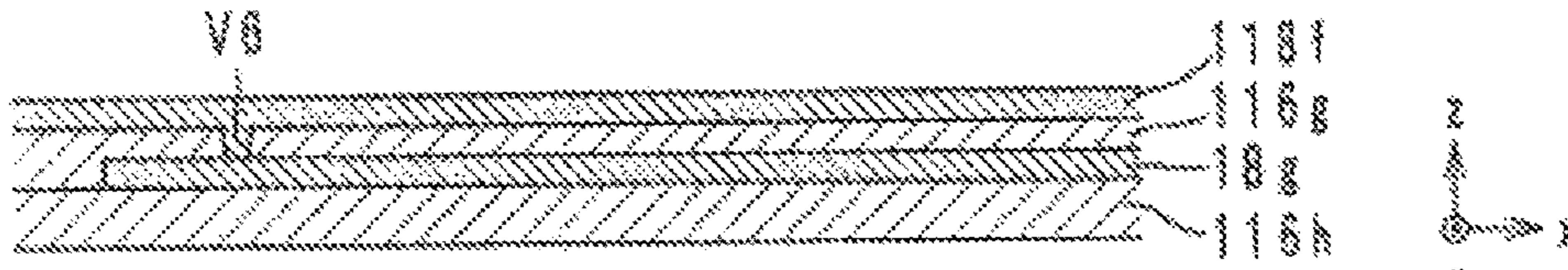


FIG.5A

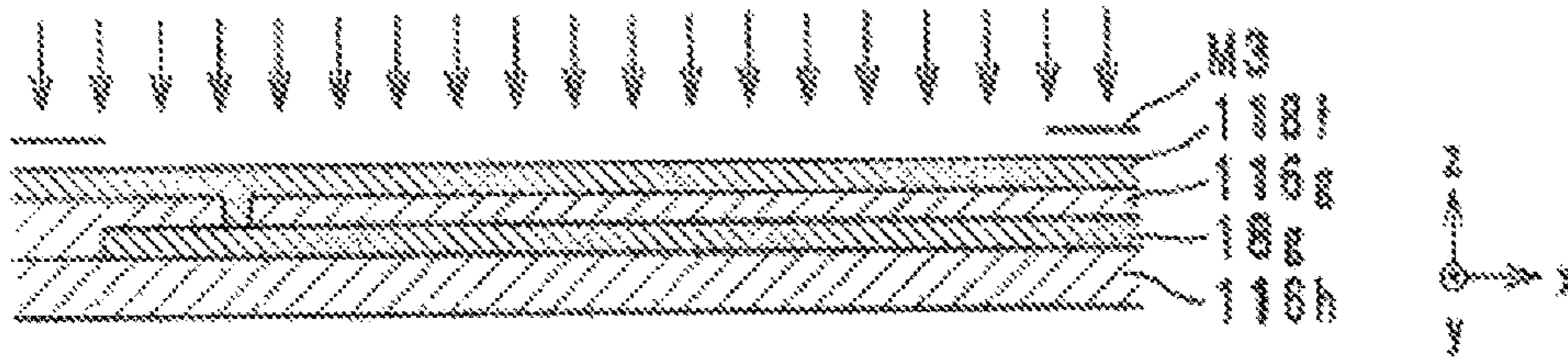


FIG.5B

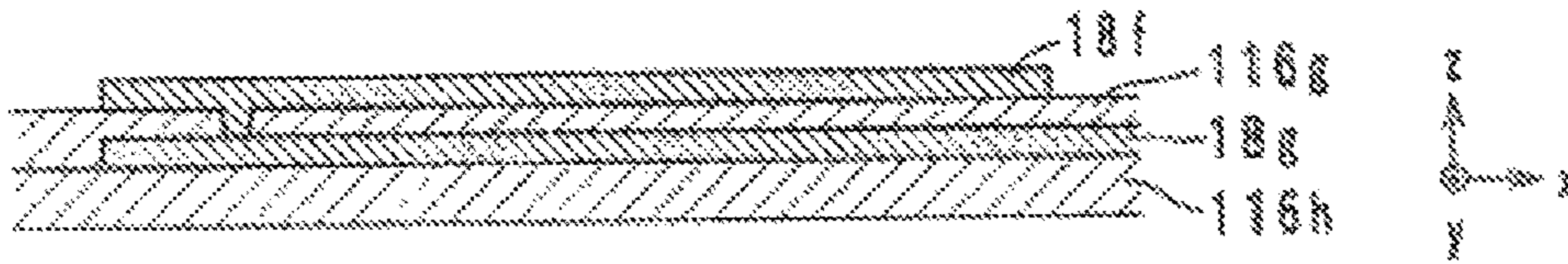


FIG.5C

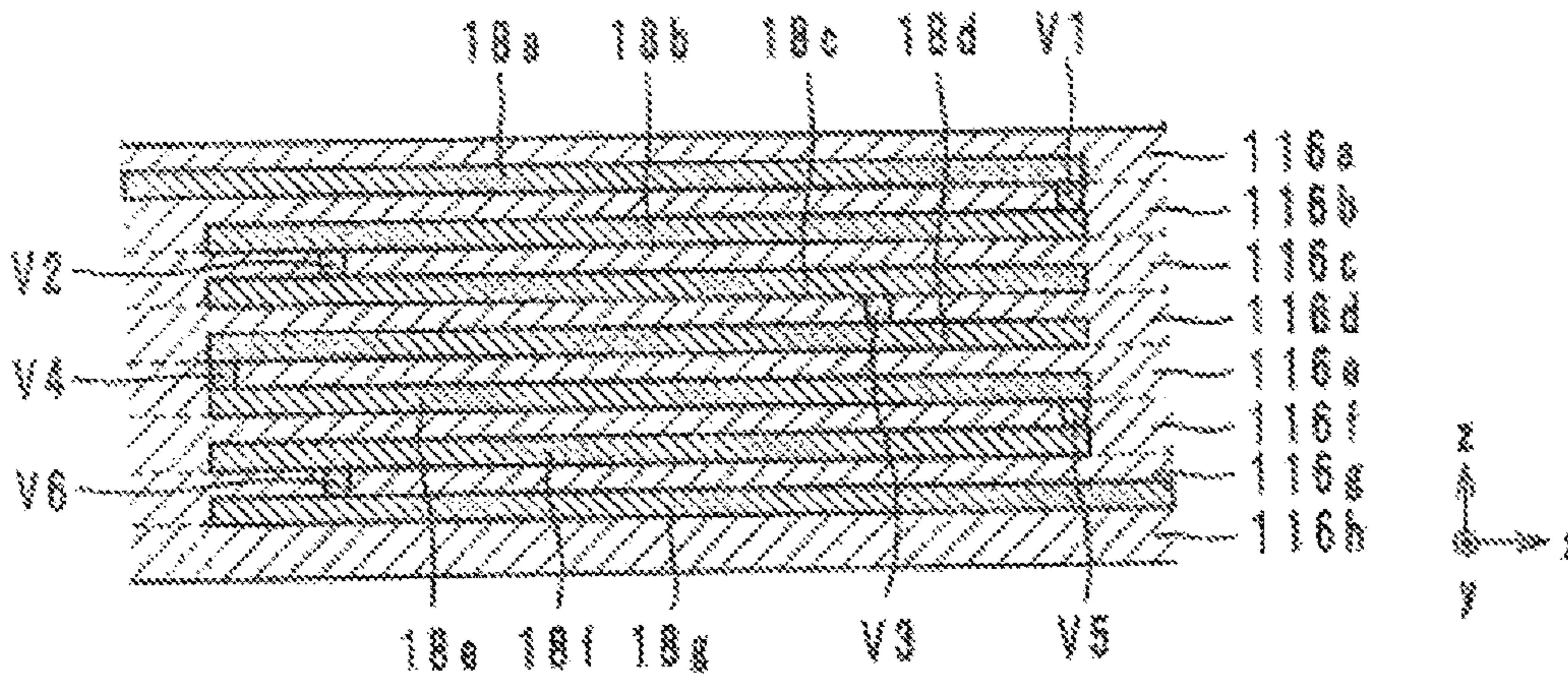


FIG.5D

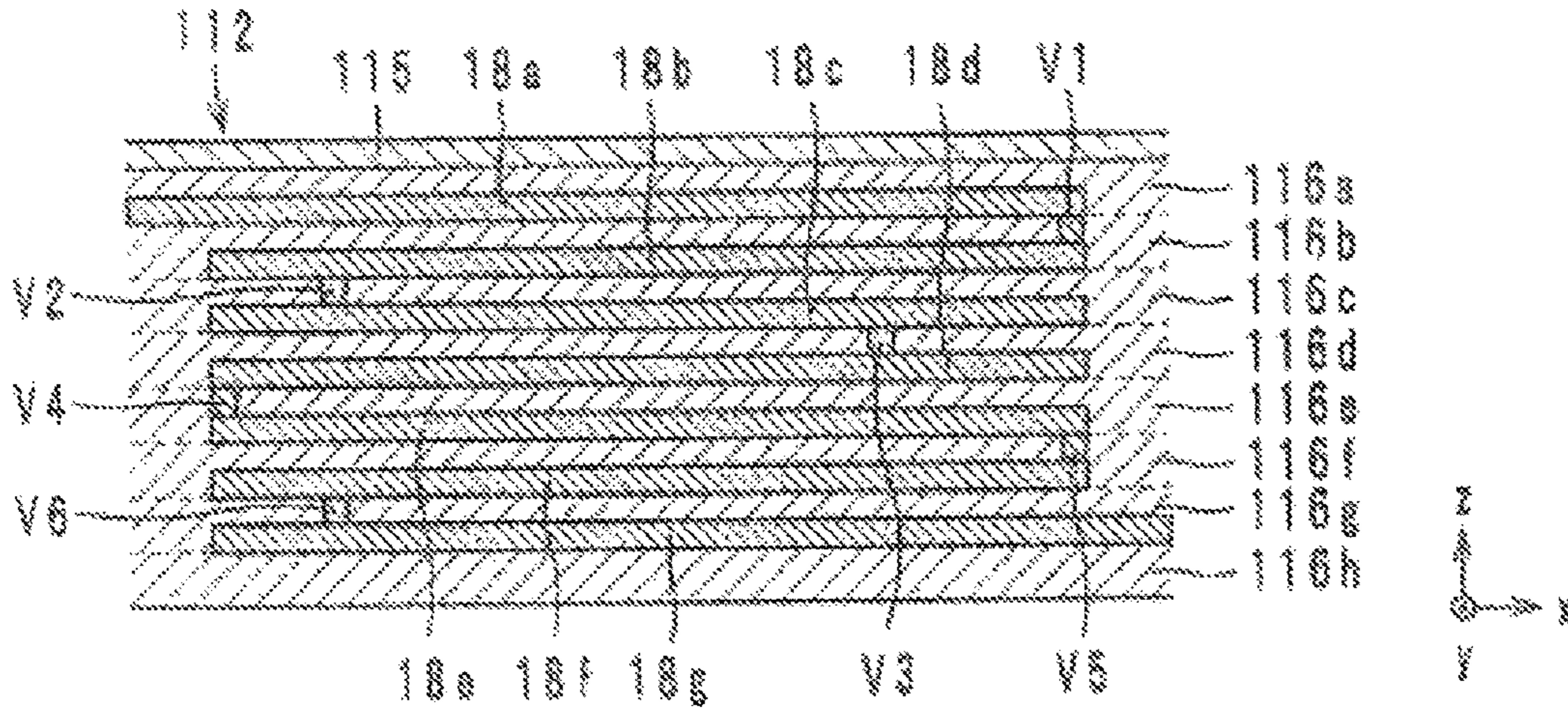


FIG.6A

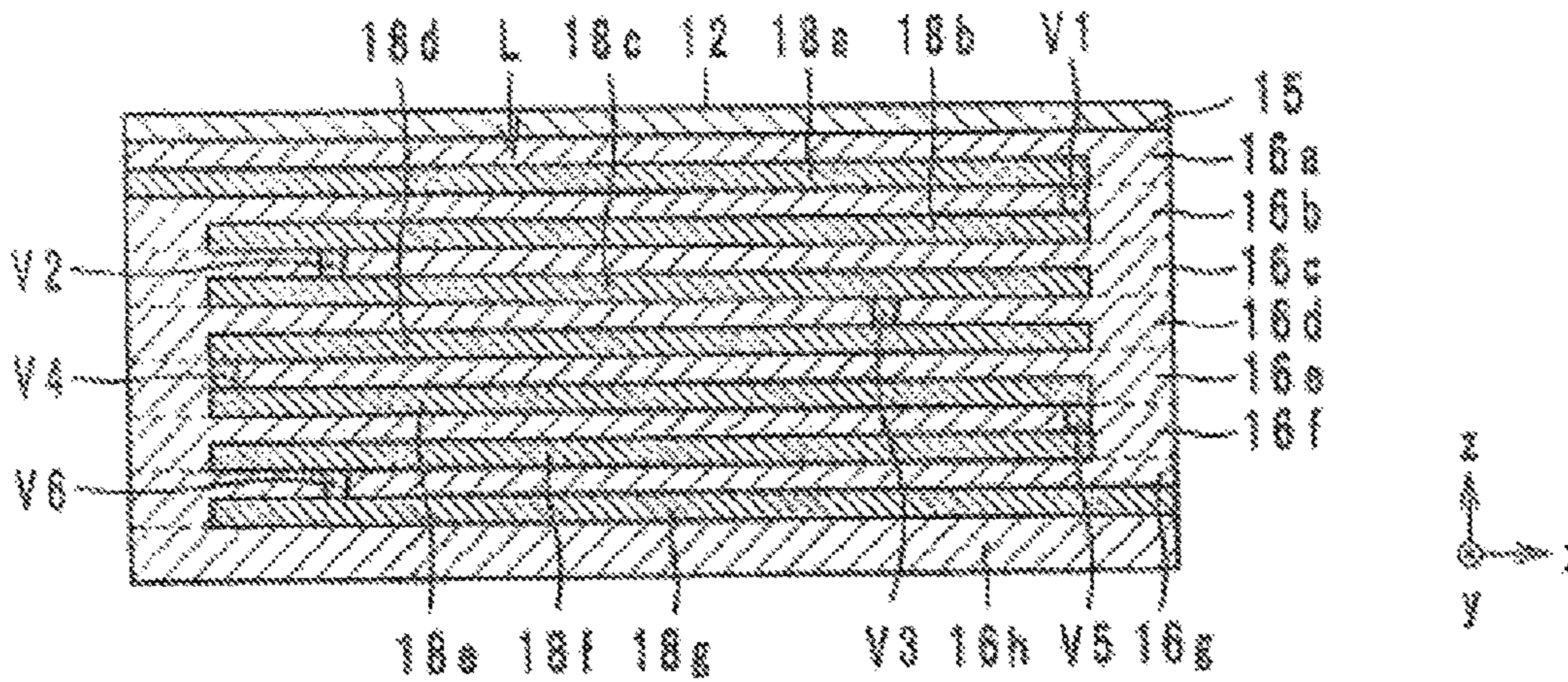


FIG.6B

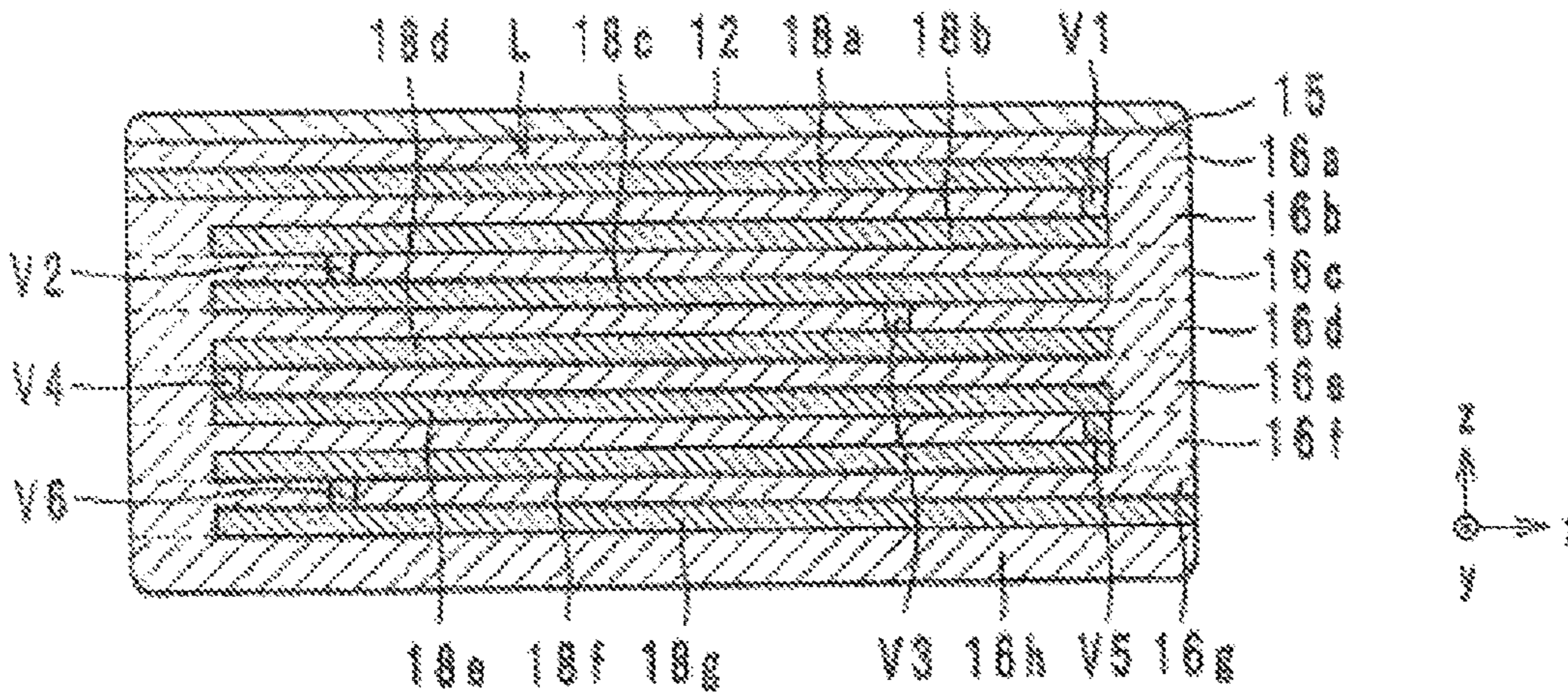


FIG.6C

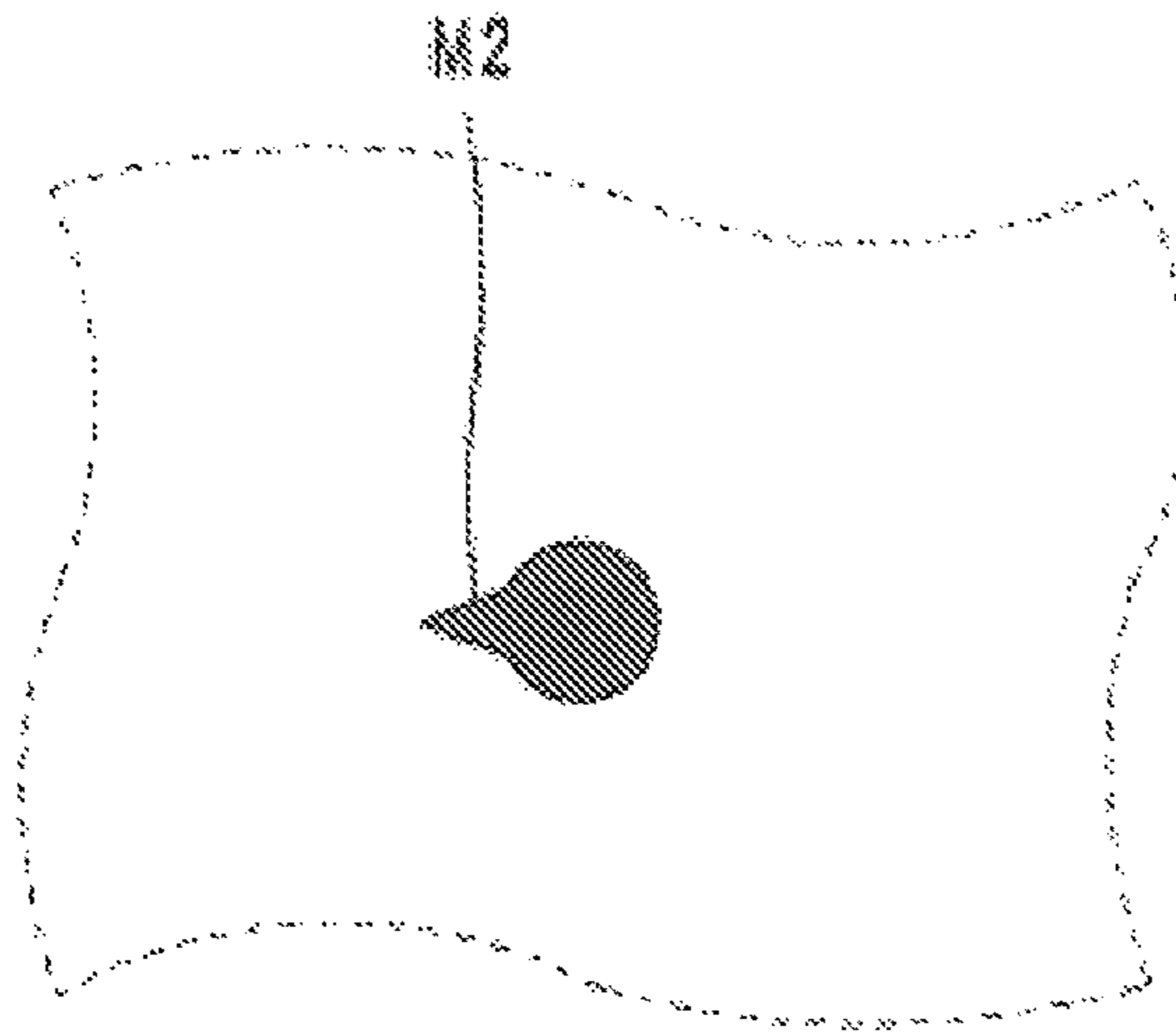


FIG. 7

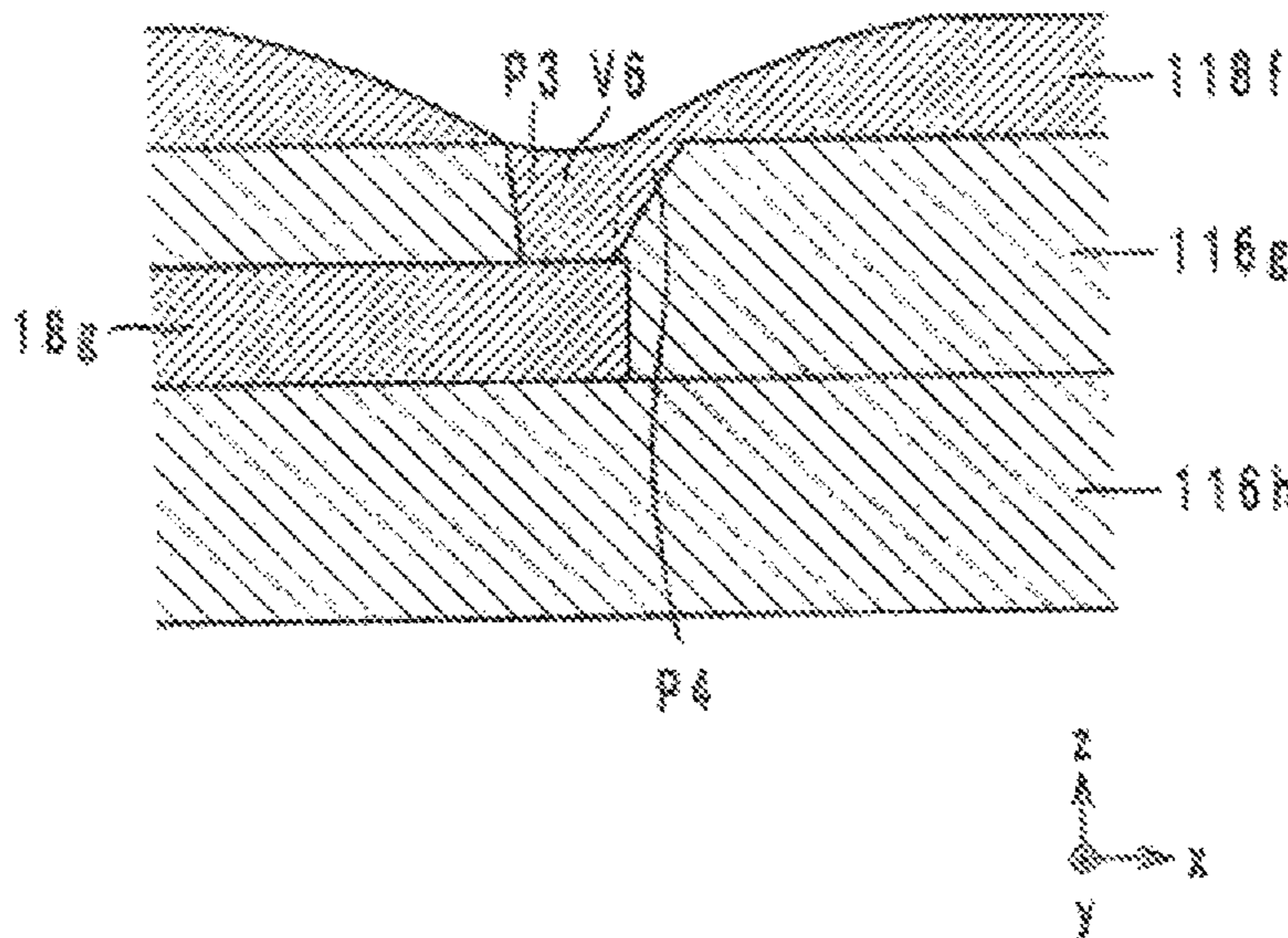
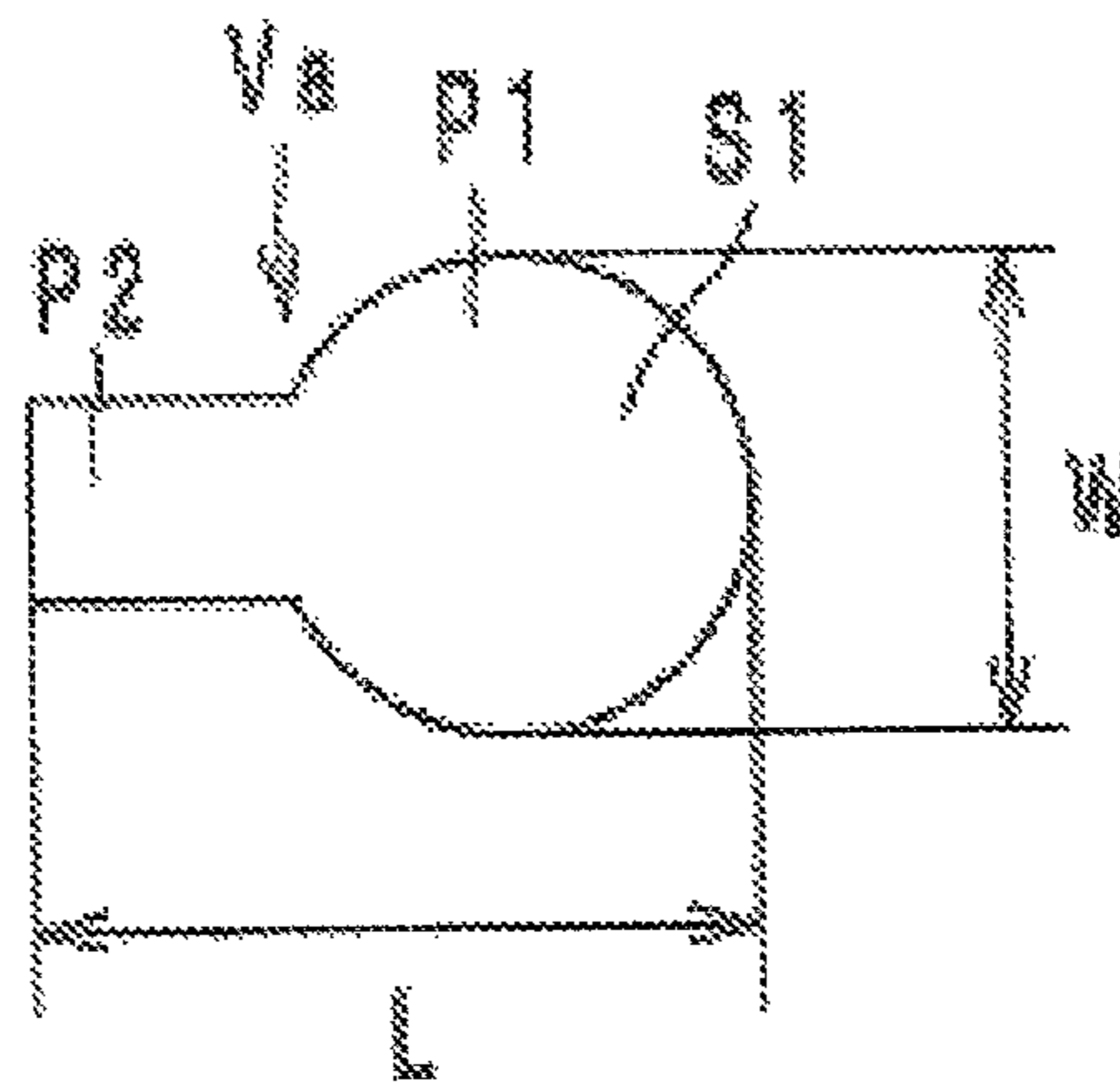
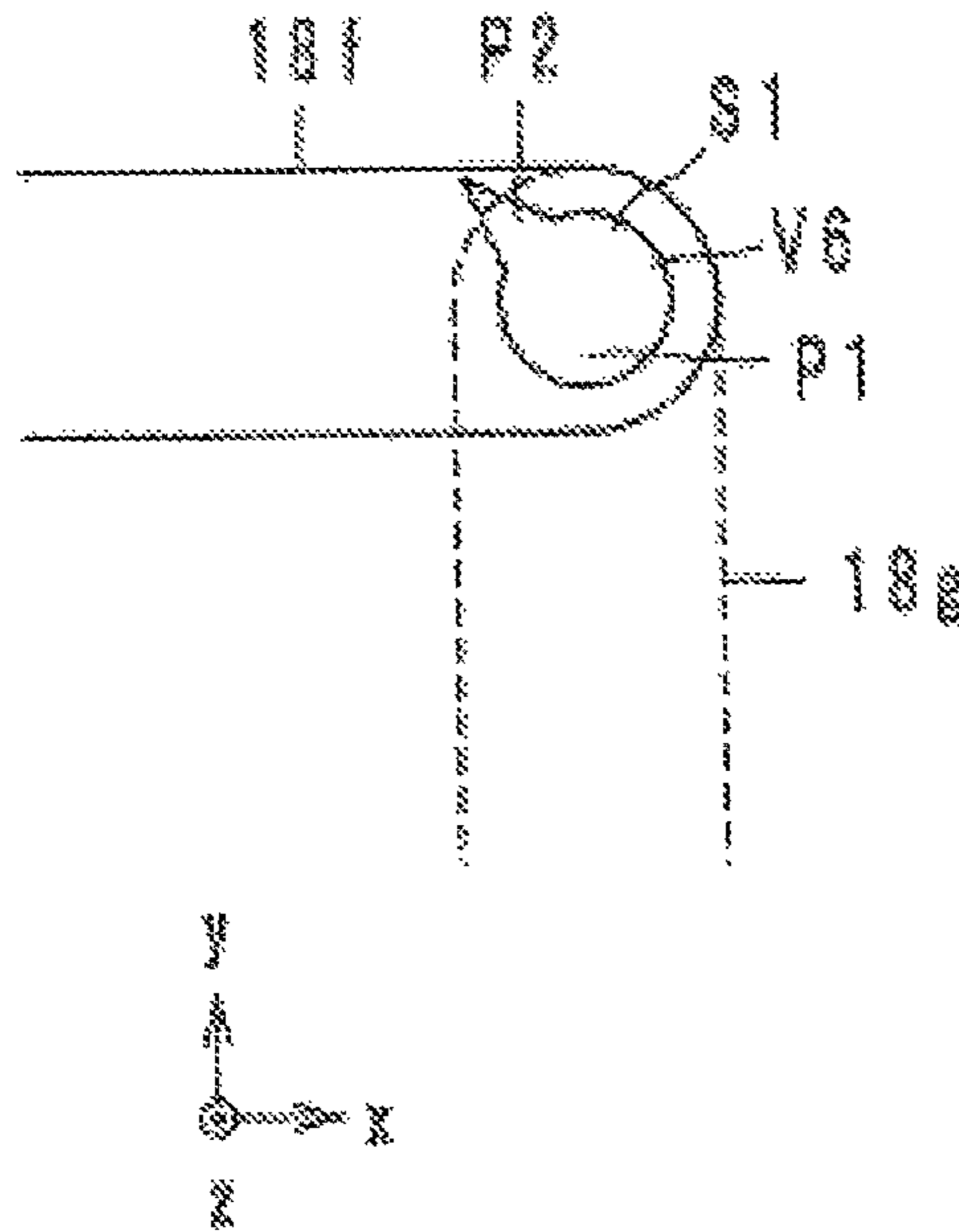


FIG. 8





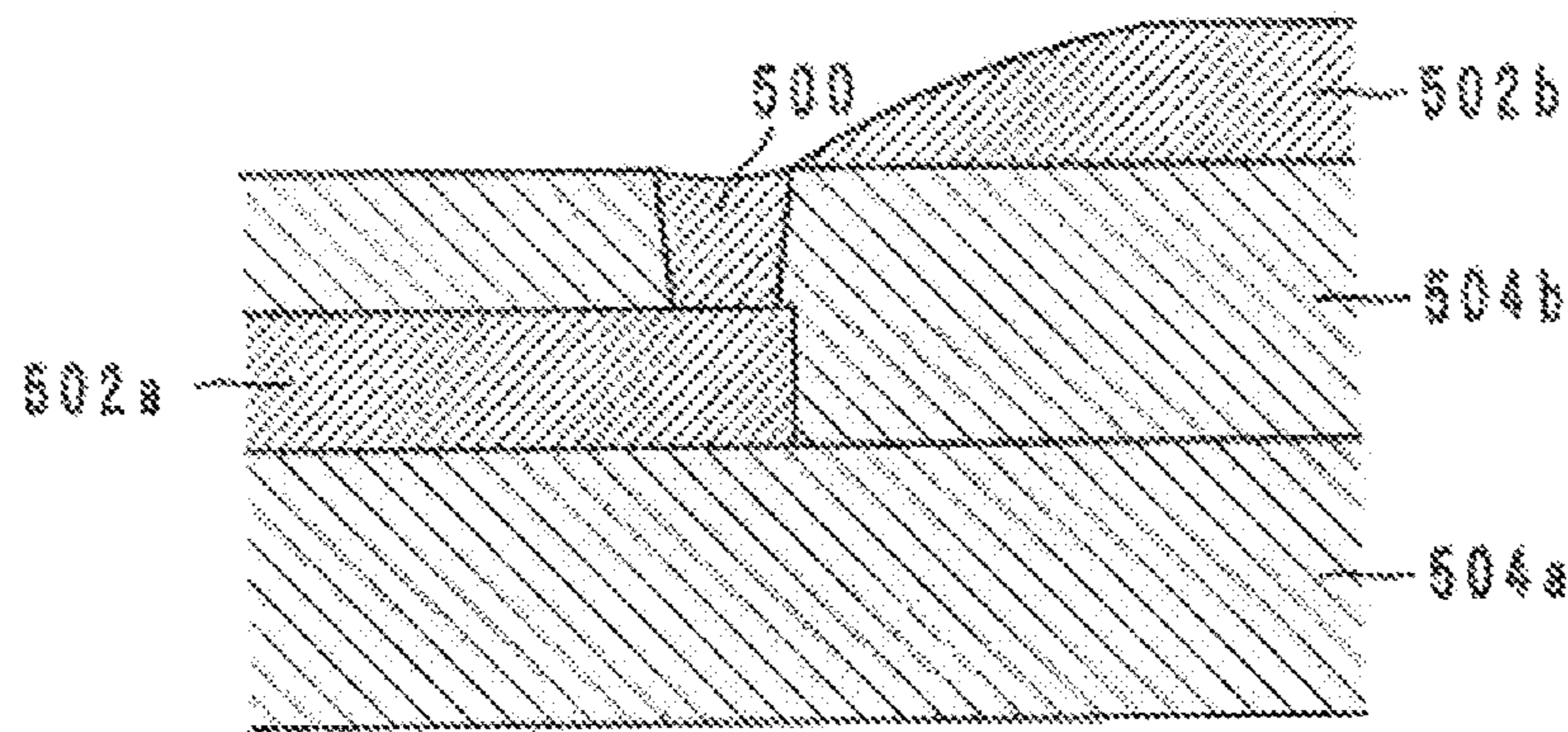


FIG.11

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## ELECTRONIC COMPONENT AND METHOD OF MANUFACTURING THE SAME

### CROSS REFERENCE TO RELATED APPLICATIONS

The present application claims priority to Japanese Patent Application No. 2012-037547 filed on Feb. 23, 2012, the entire contents of this application being incorporated herein by reference in its entirety.

### TECHNICAL FIELD

The technical field relates to electronic components and methods of manufacturing the electronic components. More specifically, the technical field relates to electronic components including a multilayer body formed by stacking a plurality of insulating layers, and to methods of manufacturing the electronic components.

### BACKGROUND

Examples of known existing electronic components include an electronic component disclosed in Japanese Unexamined Patent Application Publication No. 2000-236157. In the electronic component disclosed in Japanese Unexamined Patent Application Publication No. 2000-236157, a plurality of insulating layers are stacked on an insulating substrate. A plurality of helical coil conductors are stacked together with the insulating layers. Via hole conductors extending through the insulating layers connect the plurality of the helical coil conductors to one another. The electronic component disclosed in Japanese Unexamined Patent Application Publication No. 2000-236157 is manufactured using a photolithography method.

### SUMMARY

The present disclosure provides an electronic component in which the occurrence of disconnections between line conductor layers and via hole conductor can be suppressed and a method of manufacturing the electronic component.

An electronic component according to an embodiment of the present disclosure includes: a multilayer body formed by stacking a plurality of insulating layers including a first insulating layer and a second insulating layer; a conductor layer provided on the first insulating layer; a line conductor layer provided on the second insulating layer, which is provided on an upper side of the first insulating layer in a stacking direction; and a via hole conductor that connects an end portion of the line conductor layer to the conductor layer and that extends through the second insulating layer in the stacking direction. In the via hole conductor, a connection surface connected to the line conductor layer is formed of a circular portion and a protrusion. The protrusion protrudes from the circular portion in a first direction in which the line conductor layer extends from the end portion.

A method of manufacturing the electronic component described above includes: forming the first insulating layer; forming the conductor layer on the first insulating layer; forming, on the conductor layer, the second insulating layer in which the via hole connected to the conductor layer is formed; and forming the via hole conductor by filling a conductor into the via hole and forming the line conductor layer on the second insulating layer, using a photolithography method. In the forming of the second insulating layer, the via hole conductor having an upper end surface formed of a circular

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portion and a protrusion protruding from the circular portion in the first direction is formed.

Embodiments according to the present disclosure can suppress the occurrence of disconnections between line conductor layers and via hole conductor layers.

### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a transparent view of an electronic component according to an exemplary embodiment.

FIG. 2 is a perspective view of coil conductor layers and a via hole conductor.

FIGS. 3A to 3D are sectional process diagrams for illustrating manufacture of the electronic component.

FIGS. 4A to 4D are sectional process diagrams for illustrating manufacture of the electronic component.

FIGS. 5A to 5D are sectional process diagrams for illustrating manufacture of the electronic component.

FIGS. 6A to 6C are sectional process diagrams for illustrating manufacture of the electronic component.

FIG. 7 is a diagram illustrating a photo mask.

FIG. 8 is a process diagram illustrating the details of a process step illustrated in FIG. 5A.

FIG. 9 is a diagram illustrating a via hole conductor and coil conductor layers according a modification.

FIG. 10 is a diagram of a via hole conductor according to a second modification when viewed in plan from the z-axis direction.

FIG. 11 is a sectional structure diagram of a via hole conductor, coil conductor patterns, and insulating layers.

### DETAILED DESCRIPTION

The inventors realized that in the electronic component disclosed in Japanese Unexamined Patent Application Publication No. 2000-236157, disconnections may occur between the via hole conductors and the coil conductor patterns. FIG. 11 is a sectional structure diagram of a via hole conductor 500, coil conductor patterns 502a and 502b, and insulating layers 504a and 504b.

The coil conductor pattern 502a is provided on the insulating layer 504a. The insulating layer 504b is provided on the coil conductor pattern 502a and the insulating layer 504a. The coil conductor pattern 502b is provided on the insulating layer 504b. The via hole conductor 500 extends through the insulating layer 504b in the stacking direction and connects the coil conductor pattern 502a and the coil conductor pattern 502b.

The via hole conductor 500 and the coil conductor pattern 502b described above are formed using a photolithography method. The via hole conductor 500 and the coil conductor pattern 502b shrink when the via hole conductor 500 and the coil conductor pattern 502b are dried. In particular, a portion at which the via hole conductor 500 and the coil conductor pattern 502b are connected to each other, which has a larger volume than other portions, considerably shrinks. As a result, the via hole conductor 500 shrinks in the thickness direction of the insulating layer 504b and, hence, becomes thinner than the insulating layer 504b. Consequently, disconnections may occur between the coil conductor pattern 502a and the via hole conductor 500 and between the via hole conductor 500 and the coil conductor pattern 502b.

Hereinafter, an electronic component and a method of manufacturing the electric component according to exemplary embodiments of the present disclosure that can address the above-described shortcoming will now be described with reference to the figures.

FIG. 1 is a transparent view of an electronic component 10 according to a first exemplary embodiment. Hereinafter, the stacking direction of the electronic component 10 is defined as the z-axis. When viewed in plan from the z-axis direction, the direction in which the long sides of the electronic component 10 extend is defined as the x-axis direction, and the direction in which the short sides of the electronic component 10 extend is defined as the y-axis direction. Hereinafter, viewing in plan from the positive z-axis direction is simply expressed as viewing in plan from the z-axis direction.

As illustrated in FIG. 1, the electronic component 10 includes a multilayer body 12, external electrodes 14 (14a, 14b), and a coil L.

The multilayer body 12 is shaped like a rectangular parallelepiped, and is formed by stacking rectangular insulating layers 15 and 16a to 16h (16) in this order from the positive z-axis direction side to the negative z-axis direction side, as illustrated in FIG. 1. The insulating layer 15 is stacked on furthest toward the positive side in the z-axis direction and is a surface marker layer having a marker formed thereon indicating the orientation of the multilayer body.

The coil L includes coil conductor layers 18a to 18g, sometimes collectively referred to herein as coil conductor layers 18, and via hole conductors V1 to V6, sometimes collectively referred to herein as via hole conductors V. The coil conductor layers 18a to 18g, which are respectively provided on the insulating layers 16b to 16h, are line conductor layers revolving around the respective intersections of the diagonals of the insulating layers 16b to 16h, when viewed in plan from the z-axis direction.

A first end of the coil conductor layer 18a extends to the negative x-axis direction side end surface of the multilayer body 12. A second end of the coil conductor layer 18g extends to the positive x-axis direction side end surface of the multilayer body 12.

The via hole conductors V1 to V6 respectively extend through the insulating layers 16b to 16g in the z-axis direction and connect the corresponding ends of the coil conductor layers 18a to 18g that neighbor one another in the z-axis direction. In more detail, the via hole conductor V1 connects the second end of the coil conductor layer 18a to a first end of the coil conductor layer 18b. The via hole conductor V2 connects the second end of the coil conductor layer 18b to a first end of the coil conductor layer 18c. The via hole conductor V3 connects the second end of the coil conductor layer 18c to a first end of the coil conductor layer 18d. The via hole conductor V4 connects the second end of the coil conductor layer 18d to a first end of the coil conductor layer 18e. The via hole conductor V5 connects the second end of the coil conductor layer 18e to a first end of the coil conductor layer 18f. The via hole conductor V6 connects the second end of the coil conductor layer 18f to the first end of the coil conductor layer 18g. The coil L formed in the manner described above extends in the z-axis direction in a helical shape.

The external electrode 14a covers the negative x-axis direction side end of the multilayer body 12, and is connected to the first end of the coil conductor layer 18a. The external electrode 14b covers the positive x-axis direction side end of the multilayer body 12, and is connected to the second end of the coil conductor layer 18g. As a result, the coil L is connected between the external electrodes 14a and 14b.

The electronic component 10 has a configuration described below in order to suppress the occurrence of disconnections between the coil conductor layers 18 and the via hole conductors V. The via hole conductor V6 will be described below as an example. FIG. 2 is a perspective view of the coil conductor layers 18f and 18g and the via hole conductor V6.

The insulating layer 16g (second insulating layer) is stacked on the positive z-axis direction side of the insulating layer 16h (first insulating layer). The coil conductor layer 18g (conductor layer) is provided on the insulating layer 16h. The coil conductor layer 18g extends in the x-axis direction. The coil conductor layer 18f (line conductor) is provided on the insulating layer 16g. The coil conductor layer 18f extends in the x-axis direction. The first end of the coil conductor layer 18g and the second end of the coil conductor layer 18f are superposed with each other when viewed in plan from the z-axis direction.

The via hole conductor V6 connects the second end of the coil conductor layer 18f to the first end of the coil conductor layer 18g, and extends through the insulating layer 16g in the z-axis direction. Hereinafter, a surface of the via hole conductor V6 connected to the coil conductor layer 18f is called a connection surface S1.

The connection surface S1 is formed of a circular portion P1 and a protrusion P2. The circular portion P1 is shaped like a circle when viewed in plan from the z-axis direction. The protrusion P2, when viewed in plan from the z-axis direction, protrudes from the circular portion P1 in a direction in which the coil conductor layer 18f extends from the second end of the coil conductor layer 18f (i.e., the negative x-axis direction). The protrusion P2 is shaped like a triangle. The angle  $\theta$  of the apex of the protrusion P2 is preferably between 15 degrees and 60 degrees inclusive. The optimal value of the angle  $\theta$  is 30 degrees.

As a result of the connection surface S1 being formed of the circular portion P1 and the protrusion P2, the via hole conductor V6 has the shape of a protrusion P4 combined with a truncated cone P3. The truncated cone P3 has a shape whose diameter becomes smaller from the positive z-axis direction side to the negative z-axis direction side. The protrusion P4 has the shape of a triangular pyramid in which the amount of protrusion from the truncated cone P3 becomes smaller from the positive z-axis direction side to the negative z-axis direction side. In the embodiment shown in FIG. 2, protrusion P4 protrudes from the circular portion towards a first direction in which the coil conductor layer 18f extends from its end portion. More particularly, a straight line passing through a center of the circular portion P1 and a midpoint of a width of the protrusion P2 is substantially parallel with the direction in which conductor 18f extends from an end portion of conductor 18f where the via hole conductor V6 is positioned.

Note that since the via hole conductors V1 to V5 can have the same shape as the via hole conductor V6, description thereof is not provided as it can be understood from the above description.

Hereinafter, an exemplary method of manufacturing the electronic component 10 will be described with reference to the figures. FIGS. 3A to 6C are sectional process diagrams for illustrating manufacture of the electronic component 10. FIG. 7 is a diagram illustrating a photo mask M2. FIG. 8 is a sectional process diagram illustrating the process step of FIG. 5A in detail.

First, an insulating layer 116h is formed using a photolithography method. Specifically, as illustrated in FIG. 3A, the insulating layer 116h is formed by application of a photosensitive insulating material (e.g., a photosensitive resin including glass powder) using a printing method. At this time, the insulating layer 116h is formed in such a manner that the insulating layer 116h after sintering has a thickness of 10  $\mu\text{m}$ . After that, the insulating layer 116h is dried.

Next, as illustrated in FIG. 3B, the insulating layer 116h is subjected to exposure, whereby the insulating layer 116 is

hardened. Through the process steps illustrated in FIG. 3A and FIG. 3B, the insulating layer **116h** is formed.

Next, the coil conductor layer **18g** is formed on the insulating layer **116h** using, for example, a photo lithography method. Specifically, as illustrated in FIG. 3C, a conductor layer **118g** is formed by applying a photosensitive conductive material over the whole surface of the insulating layer **116h** using a printing method. At this time, the conductor layer **118g** is formed in such a manner that the coil conductor layer **18g** after sintering has a thickness of 8  $\mu\text{m}$ . After that, the conductor layer **118g** is dried. Although not illustrated, the conductor layer **118g** shrinks while being dried. The shrinking ratio of the conductor layer **118g** is between 0.6 and 0.9 inclusive. Here, the shrinking ratio of the conductor layer **118g** is a value obtained by dividing the volume of the conductor layer **118g** after having been dried by the volume of the conductor layer **118g** before being dried.

Next, as illustrated in FIG. 3D, the conductor layer **118g** is subjected to exposure using a photo mask **M1** which allows light to pass through only a portion thereof corresponding to the coil conductor layer **18g**. As a result, only a portion of the conductor layer **118g** corresponding to the coil conductor layer **18g** is hardened.

Next, a portion of the conductor layer **118g** which has not been hardened is removed using a developing solution. As a result, the coil conductor layer **18g** is developed, as illustrated in FIG. 4A. Through the process steps illustrated in FIG. 3C, FIG. 3D, and FIG. 4A, the coil conductor layer **18g** is formed.

Next, an insulating layer **116g** in which a via hole **h6** connected to the coil conductor layer **18g** is formed is formed on the coil conductor layer **18g** using a photolithography method. Specifically, as illustrated in FIG. 4B, an insulating layer **116g** is formed by applying a photosensitive insulating material over the whole exposed surfaces of the insulating layer **116h** and the coil conductor layer **18g** using a printing method. After that, the insulating layer **116g** is dried.

Next, as illustrated in FIG. 4C, the insulating layer **116g** is subjected to exposure using the photo mask **M2** that does not allow light to pass therethrough only at a portion where the via hole conductor **V6** is to be formed, thereby hardening the insulating layer **116g**. As illustrated in FIG. 7, the photo mask **M2** is made in such a manner that a Cr plating portion having the same shape as the connection surface **S1** of the via hole conductor **V6** is formed on a transparent plate, such as a glass plate. As a result, the insulating layer **116g** excluding a portion thereof where the via hole conductor **V6** is to be formed is hardened.

Next, a portion of the insulating layer **116g** which has not been hardened is removed using a development solution. As a result, referring to FIG. 4D, the via hole **h6** is formed in the insulating layer **116g**. Note that as a result of using the photo mask **M2** illustrated in FIG. 7, the top end of the via hole **h6** is formed of a circular portion and a protrusion protruding from the circular portion in the negative x-axis direction. Further, the via hole **h6** becomes thinner, or has decreasing area in the x-axis and y-axis plane in the negative z-axis direction. This is because, in the process illustrated in FIG. 4D, it becomes harder for a development solution to reach a deeper portion of the insulating layer **116g**. Through the process steps illustrated in FIG. 4B to 4D, the insulating layer **116g** is formed.

Next, using a photolithography method, the via hole **h6** is filled with a conductor, thereby forming the via hole conductor **V6** having a diameter of 50  $\mu\text{m}$ , and the coil conductor layer **18f** is formed on the insulating layer **116g**. Specifically, as illustrated in FIG. 5A, a conductor layer **118f** made of a photosensitive conductive material is applied over the whole

surface of the insulating layer **116g** using a printing method. After that, the conductor layer **118f** is dried. As illustrated in FIG. 8, the conductor layer **118f** and the via hole conductor **V6** shrink while being dried. In particular, the via hole conductor **V6**, which has a larger volume per unit area when viewed in plan than the rest of the conductor layer **118f**, considerably shrinks. However, the connection surface **S1** of the via hole conductor **V6** is formed of the circular portion **P1** and the protrusion **P2**. Hence, the via hole conductor **V6** has the shape of the protrusion **P4** combined with the truncated cone **P3**, as a result of the connection surface **S1** being formed of the circular portion **P1** and the protrusion **P2**. Consequently, even when the via hole conductor **V6** shrinks, since the protrusion **P4** is shaped like a triangular pyramid, the volume gradually decreases in the protruding direction and, hence, the degree of shrinkage due to drying also gradually decreases. In other words, the degree of shrinkage of the protrusion **P4** gradually decreases in the protruding direction. Hence, connection between the via hole conductor **V6** and the conductor layer **118f** is maintained, and disconnection is prevented from occurring.

Next, as illustrated in FIG. 5B, the conductor layer **118f** is subjected to exposure using a photo mask **M3** which allows light to pass through a portion thereof corresponding to the coil conductor layer **18f**. As a result, only a portion of the conductor layer **118f** corresponding to the coil conductor layer **18f** is hardened.

Next, a portion of the conductor layer **118f** which has not been hardened is removed using a development solution. As a result, the coil conductor layer **18f** is developed as illustrated in FIG. 5C.

After that, by repeating the process steps illustrated in FIG. 4B to FIG. 5C, insulating layers **116a** to **116f**, the coil conductor layers **18a** to **18e**, and the via hole conductors **V1** to **V5** are formed, as illustrated in FIG. 5D.

Next, as illustrated in FIG. 6A, an insulating layer **115** made of a photoconductive material is applied using a printing method. Then, the insulating layer **115** is dried. As a result, a mother multilayer body **112** is obtained.

Next, as illustrated in FIG. 6B, a plurality of multilayer bodies **12** are obtained by cutting the mother multilayer body **112** using a dicer or the like. Note that the mother multilayer body **112** is cut in such a manner that the multilayer bodies **12** each having a size of 0.3 mm $\times$ 0.3 mm $\times$ 0.6 mm are obtained after sintering. After that, the multilayer bodies **12** are sintered at a predetermined temperature.

Next, as illustrated in FIG. 6C, the multilayer bodies **12** are subjected to barrel finishing, whereby the edges of the multilayer bodies **12** are chamfered.

Finally, as illustrated in FIG. 1, the external electrodes **14a** and **14b** are formed. Specifically, underlying electrodes are formed by applying conductive paste made of Ag. The external electrodes **14a** and **14b** are formed by plating the underlying electrodes with Ni and Sn. Through the process steps described above, the electronic component **10** is manufactured.

The electronic component **10** configured as described above and the method of manufacturing the electronic component **10** allow for suppression of the occurrence of disconnections between the coil conductor layers **18** and the via hole conductors **V**. In more detail, as illustrated in FIG. 8, the conductor layer **118f** and the via hole conductor **V6** shrink while being dried. In particular, the via hole conductor **V6** considerably shrinks since the volume per unit area is large when the conductor layer **118f** is viewed in plan.

Hence, the connection surface **S1** of the via hole conductor **V6** is formed of the circular portion **P1** and the protrusion **P2**.

The protrusion P2 protrudes in a direction in which the coil conductor layer 18f obtained by developing the conductor layer 118f extends. As a result, the via hole conductor V6 has the shape of the protrusion P4 combined with the truncated cone P3. Hence, even when the conductor layer 118f shrinks, connection between the protrusion P4 and the conductor layer 118f can be maintained. Consequently, disconnection between the conductor layer 118f and the via hole conductor V6 can be prevented from occurring.

In the electronic component 10, the angle  $\theta$  of the apex of the protrusion P2 is preferably between 15 degrees and 60 degrees inclusive. As a result of the angle  $\theta$  being 15 degrees or more, a developing solution is allowed to easily penetrate into the protrusion P4, and the protrusion P4 shaped like a triangular pyramid having a sufficiently large size is formed. As a result of the angle  $\theta$  being 60 degrees or less, the diameter of the via hole conductors V is prevented from becoming too large. When the angle  $\theta$  is larger than 60 degrees, a developing solution penetrates into the protrusion P4 too much and the protrusion P4 becomes too large. In this case, the length of the protrusion P4 becomes too large and the protrusion P4 may protrude from the coil conductor layer 18 and come in contact with another coil conductor layer 18. Hence, it is preferable that the angle  $\theta$  be 60 degrees or less. Note that the optimal value of the angle  $\theta$  is 30 degrees.

Although ways of suppressing disconnection may include forming the coil conductor layers 18 in such a manner as to have a large thickness in advance, when the ratio of the thickness of the insulating layers 16 in the z-axis direction to the thickness of the coil conductor layers 18 in the z-axis direction is 1.0 or less, the thickness of the insulating layers 16 in the z-axis direction becomes small. Hence, the distance between the coil conductor layers 18 becomes small and stray capacitance between the coil conductor layers 18 becomes large. As a result, the Q characteristics of the coil of the electronic component 10 are degraded. Consequently, in the electronic component 10, it is preferable that the ratio of the thickness of the insulating layers 16 in the z-axis direction to the thickness of the coil conductor layers 18 in the z-axis direction be larger than 1.0.

It is preferable that the thickness of the conductor layers 118 in the z-axis direction before sintering be larger than or equal to 6  $\mu\text{m}$ . This is because when the thickness of the conductor layers 118 in the z-axis direction before sintering is smaller than 6  $\mu\text{m}$ , it is difficult to form the coil conductor layers 18.

Hereinafter, a via hole conductor V6 according to a first exemplary modification will be described with reference to the figures. FIG. 9 is a diagram illustrating the via hole conductor V6 and coil conductor layers 18g and 18f according to the first modification.

When the coil conductor layer 18g extends in the y-axis direction and the coil conductor layer 18f extends in the x-axis direction, the via hole conductor V6 is provided in a corner formed by the coil conductor layers 18f and 18g. In this case, the protrusion P2 may face in a slanting direction with respect to the x-axis direction. As can be seen in FIG. 9, the protrusion P2 faces towards a direction in which conductor 18f extends from an end portion of conductor 18f. However, it is required that the protrusion P2 do not protrude from the coil conductor layer 18f when viewed in plan from the z-axis direction and that the protrusion P2 form an acute angle with the negative x-axis direction. That is, it can be seen that a straight line passing through a center of the circular portion P1 and a midpoint of a width of the protrusion P2 (i.e., the apex) forms an acute angle with a longitudinal axis of the conductor 18f.

Hereinafter, a via hole conductor Va according a second exemplary modification and a via hole conductor Vb according to a third exemplary modification will be described with reference to the figures. FIG. 10 is a diagram of the via hole conductor Va according to the second modification when viewed in plan from the z-axis direction.

As illustrated in FIG. 10, the protrusion P2 may be shaped like a rectangle. Furthermore, there may be a plurality of protrusions.

The electronic component 10 configured as described above and the manufacturing method are not limited to the electronic component 10 and the manufacturing method according to the embodiments described above, and various modifications are possible within the scope of the disclosure.

The dimensions of the electronic component 10 are exemplary, and not limited to those described in the embodiments. Examples of the dimensions of the electronic component 10 will be described below.

The size of the electronic component 10: 0.2 mm $\times$ 0.2 mm $\times$ 0.6 mm, 0.5 mm $\times$ 0.5 mm $\times$ 1.0 mm

The thickness of the coil conductor layers 18: 6  $\mu\text{m}$ -13  $\mu\text{m}$  after sintering (8  $\mu\text{m}$ -17  $\mu\text{m}$  before sintering)

The thickness of the insulating layers 16: 7  $\mu\text{m}$ -15  $\mu\text{m}$  after sintering (9  $\mu\text{m}$ -30  $\mu\text{m}$  before sintering)

The diameter of the via hole conductors V: 20  $\mu\text{m}$ -65  $\mu\text{m}$  after sintering

As described above, embodiments consistent with the present disclosure are useful in electronic components and methods of manufacturing them, and in particular have an advantage in suppression of disconnections between line conductor layers and via hole conductor layers.

What is claimed is:

1. An electronic component comprising:

a multilayer body formed by stacking a plurality of insulating layers including a first insulating layer and a second insulating layer;

a conductor layer provided on the first insulating layer;

a line conductor layer provided on the second insulating layer, which is provided on an upper side of the first insulating layer in a stacking direction; and

a via hole conductor that connects an end portion of the line conductor layer to the conductor layer and that extends through the second insulating layer in the stacking direction,

wherein, in the via hole conductor, a connection surface connected to the line conductor layer is formed of a circular portion and a protrusion, and

wherein the protrusion, when viewed in plan from the stacking direction, protrudes from a part of an outer edge of the circular portion towards a first direction in which the line conductor layer extends from the end portion, the protrusion, when viewed in plan from the stacking direction, has a triangular shape, and

an angle of an apex of the protrusion is larger than or equal to 15 degrees and smaller than or equal to 60 degrees.

2. The electronic component according to claim 1, wherein an area of the protrusion in a plane perpendicular to the stacking direction decreases in the stacking direction from line conductor layer to the conductor layer.

3. The electronic component according to claim 1, wherein a straight line passing through a center of the circular portion and a midpoint of a width of the protrusion is substantially parallel with the first direction.

4. A method of manufacturing the electronic component

according to claim 1, the method comprising:

forming the first insulating layer;

forming the conductor layer on the first insulating layer;

forming, on the conductor layer, the second insulating layer in which the via hole connected to the conductor layer is formed; and  
forming the via hole conductor by filling a conductor into the via hole and forming the line conductor layer on the second insulating layer, using a photolithography method,  
wherein, in the forming of the second insulating layer, the via hole conductor having an upper end surface formed of a circular portion and a protrusion protruding from the circular portion in the first direction is formed.

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